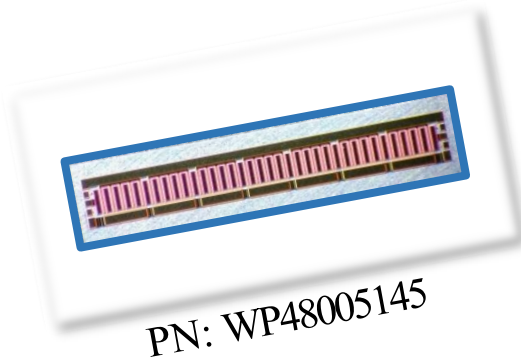




WP48005145

145W, 48V GaN HEMT Die



The WP48005145 is a 145W gallium nitride (GaN) High Electron Mobility Transistor (HEMT). This GaN HEMT is a wideband transistor optimized for 3.5GHz operation in a user-friendly device for high bandwidth applications. Gallium nitride (GaN) HEMT is a device optimized for 5G. GaN HEMT resistance is only 1/10 that of silicon transistors, making it capable of switching frequencies faster for greater energy efficiency.

Features

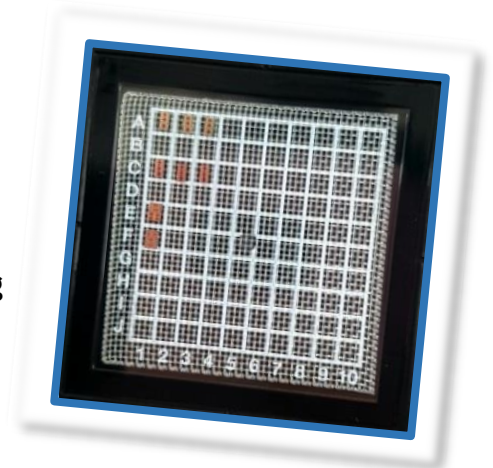
- Up to 8 GHz Operation
- 14.0 dB Typical Small Signal Gain @ 3.5 GHz
- 145 W Typical Psat @3.5GHz
- 48V Operation
- High Breakdown Voltage
- High Breakdown Voltage
- High Efficiency
- Reliability Monitoring Supporting

Applications

- U/VHF Amplifiers
- Broadband Amplifiers
- Base Station Communications
- Drone, UAV
- WiMAX, LTE, WCDMA, GSM
- WPT, V2X
- Radar application

Packaging Information

- Bare die are shipped in Wafer-level with Expander Ring or Gel-Pak® containers.
- Possible UV Curing for Wafer-level with dicing saw



Absolute Maximum Ratings (not simultaneous) at 25 °C

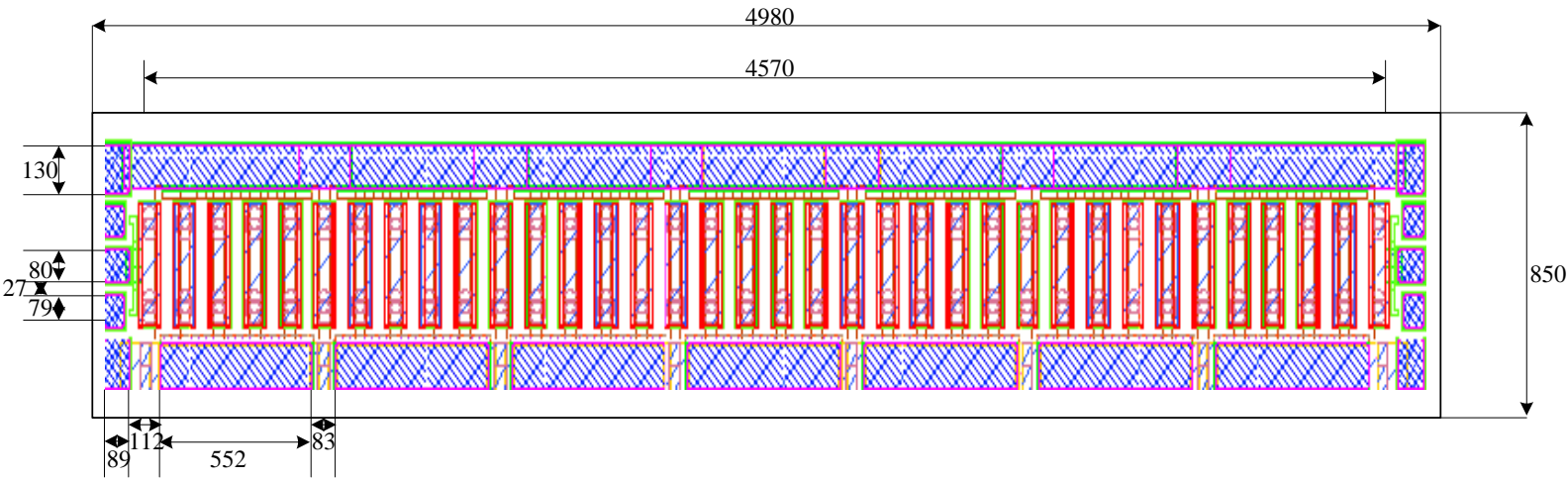
Parameter	Parameter	Typical Value	Units	Conditions
Threshold voltage @ Id=1mA/mm, Vd=10V	V _{to}	-3.4	V	25°C
Breakdown voltage @ Id=1mA/mm	V _{DG}	160	V	25°C
Drain-source current, Id @ Vd=10V, Vg=0	I _{dss}	800	mA/mm	25°C
Operating Junction Temperature	T _J	225	°C	
Storage Temperature	T _{STG}	-65, +150	°C	
Thermal Resistance, Junction to Case (packaged)	R _{θJC}		°C/W	
Thermal Resistance, Junction to Case (die only)	R _{θJC}		°C/W	
Mounting Temperature (30 seconds)	T _S	320	°C	30 seconds

Electrical Characteristics (Frequency = 3.5 GHz unless otherwise stated; TC = 25 °C)

Parameter	Parameter	Typical Value	Units	Conditions
DC Characteristics				
Ohmic contact resistance	RC	0.3	Ohm-mm	25°C
Maximum Drain-source current, Id @ Vd=10V, Vg=1V (1X125µm device)	I _{dmax}	1000	mA/mm	25°C
Max. trans-conductance, @ Vd=10V, Vg=-4V ~ -1V (1X125µm device)	GM_PEAK	290	mS/mm	25°C
Maximum Drain-source current, Id @ Vd=10V, Vg=1V (1X125µm device)	I _{dmax}	1000	mA/mm	25°C
RF Characteristics				
Small Signal Gain	G _{SS}	>12	dB	V _{DD} =48V, I _{DQ} =300mA
Saturated Power Output	P _{SAT}	145	W	V _{DD} =48V, I _{DQ} =300mA
Drain Efficiency	η	>60	%	V _{DD} =48V, I _{DQ} =300mA
Intermodulation Distortion	IM3	<-30	dBc	V _{DD} =48V, I _{DQ} =300mA
Output Mismatch Stress	VSWR	10:1	ψ	



DIE Dimensions (units in microns)



Overall die size 4980 x 850 (+0/-50) microns, die thickness 100 (+/- 10) microns.
All Gate and Drain pads must be wire bonded for electrical connection.

Assembly Notes:

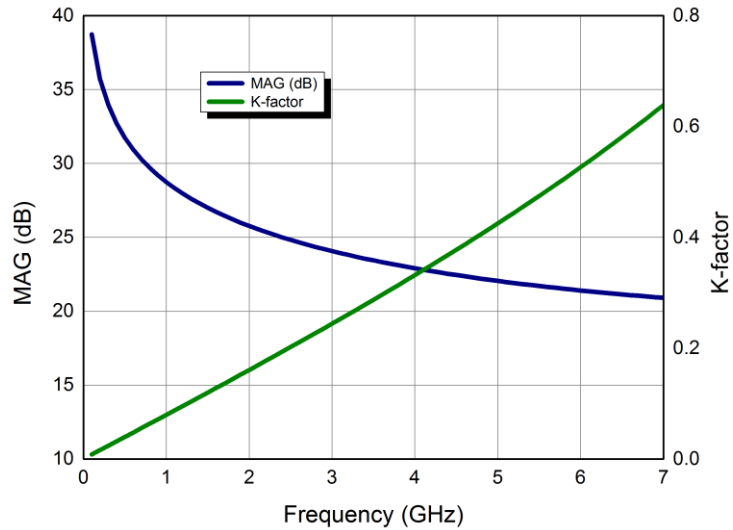
- Recommended solder is AuSn (80/20) solder. Refer to Wavepia's guide for the Eutectic Die Bond Procedure
- Vacuum collet is the preferred method of pick-up.
- The backside of the die is the Source (ground) contact.
- Die back side gold plating is 5 microns thick minimum.
- Thermosonic ball or wedge bonding are the preferred connection methods.
- Gold wire must be used for connections.



Typical Performance

Simulated Maximum Available Gain (MAG) and K Factor of the WP48005145

$V_{DD} = 48 \text{ V}$, $I_{DQ} = 750 \text{ mA}$

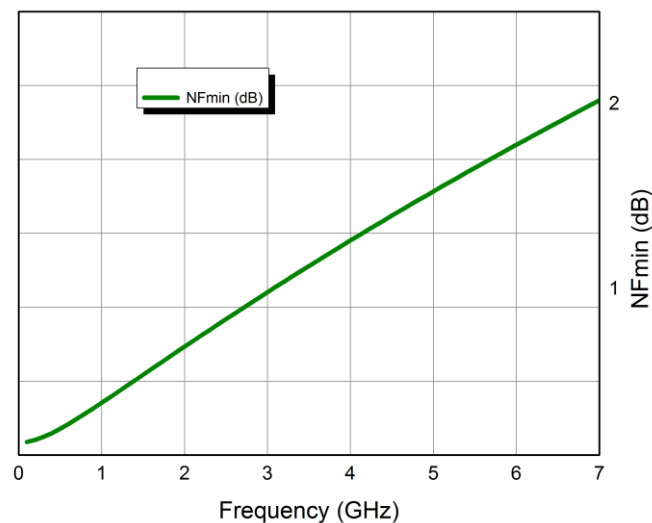


Intrinsic die parameters - reference planes at centers of gate and drain bonding pads. No wire bonds assumed.

Typical Performance

Simulated Minimum Noise Figure of the WP48005145

$V_{DD} = 48 \text{ V}$, $I_{DQ} = 750 \text{ mA}$





Typical Die S-Parameters

(Small Signal, $V_{DS} = 48\text{ V}$, $I_{DQ} = 750\text{ mA}$, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
100MHz	0.967509	-133.448	44.70958	111.3019	0.00599	21.44743	0.707258	-168.099
200MHz	0.963456	-155.674	23.71574	98.78584	0.006354	9.076837	0.740463	-172.942
300MHz	0.962686	-163.593	15.97483	93.32661	0.006419	3.763125	0.748182	-174.475
400MHz	0.962523	-167.602	12.00504	89.79449	0.006431	0.376556	0.751904	-175.049
500MHz	0.962574	-170.01	9.595284	87.05576	0.006423	-2.21659	0.75467	-175.23
600MHz	0.962734	-171.612	7.976637	84.72289	0.006405	-4.40382	0.757249	-175.219
700MHz	0.962965	-172.75	6.813447	82.62868	0.006381	-6.35235	0.759895	-175.103
800MHz	0.963252	-173.599	5.936254	80.68974	0.006351	-8.14553	0.762704	-174.929
900MHz	0.963583	-174.255	5.25037	78.86019	0.006316	-9.82924	0.765711	-174.723
1000MHz	0.963954	-174.777	4.698777	77.11296	0.006278	-11.4306	0.768922	-174.5
1100MHz	0.964359	-175.201	4.245101	75.43117	0.006235	-12.9663	0.772331	-174.271
1200MHz	0.964794	-175.552	3.865054	73.80391	0.006189	-14.4475	0.775924	-174.042
1300MHz	0.965257	-175.848	3.541801	72.22389	0.00614	-15.8813	0.779683	-173.819
1400MHz	0.965742	-176.101	3.263306	70.68607	0.006087	-17.2727	0.783588	-173.605
1500MHz	0.966248	-176.32	3.020737	69.18694	0.006032	-18.6254	0.787619	-173.402
1600MHz	0.966772	-176.512	2.807466	67.72394	0.005975	-19.9418	0.791755	-173.213
1700MHz	0.96731	-176.681	2.61842	66.2952	0.005916	-21.2237	0.795976	-173.037
1800MHz	0.96786	-176.833	2.44965	64.89929	0.005854	-22.4727	0.800262	-172.876
1900MHz	0.968419	-176.969	2.298038	63.53512	0.005791	-23.6897	0.804594	-172.729
2000MHz	0.968986	-177.093	2.161084	62.20177	0.005726	-24.8758	0.808955	-172.598
2100MHz	0.969557	-177.207	2.036762	60.89851	0.00566	-26.0316	0.813328	-172.481
2200MHz	0.970131	-177.311	1.923411	59.62466	0.005593	-27.1577	0.817698	-172.379
2300MHz	0.970707	-177.408	1.819657	58.37963	0.005525	-28.2548	0.822052	-172.291
2400MHz	0.971281	-177.499	1.72435	57.16287	0.005456	-29.3234	0.826378	-172.215
2500MHz	0.971853	-177.585	1.636523	55.97383	0.005386	-30.3641	0.830663	-172.153
2600MHz	0.972421	-177.665	1.555354	54.812	0.005316	-31.3773	0.834899	-172.103
2700MHz	0.972984	-177.742	1.480139	53.67685	0.005245	-32.3635	0.839077	-172.064
2800MHz	0.97354	-177.815	1.410274	52.56786	0.005175	-33.3234	0.84319	-172.035
2900MHz	0.97409	-177.885	1.345235	51.48451	0.005104	-34.2573	0.847232	-172.017
3000MHz	0.974631	-177.952	1.284565	50.42625	0.005034	-35.1658	0.851197	-172.008
3100MHz	0.975164	-178.016	1.227864	49.39256	0.004963	-36.0494	0.85508	-172.008
3200MHz	0.975687	-178.079	1.17478	48.38288	0.004893	-36.9087	0.85888	-172.016
3300MHz	0.9762	-178.139	1.125002	47.39668	0.004823	-37.7442	0.862592	-172.031
3400MHz	0.976703	-178.198	1.078253	46.4334	0.004754	-38.5564	0.866215	-172.053
3500MHz	0.977195	-178.255	1.034288	45.49249	0.004685	-39.346	0.869747	-172.081
3600MHz	0.977676	-178.311	0.992886	44.57339	0.004616	-40.1133	0.873188	-172.115
3700MHz	0.978146	-178.365736	0.95385	43.67556	0.004548	-40.8589	0.876537	-172.155
3800MHz	0.978604	-178.419106	0.917	42.79844	0.004481	-41.5835	0.879795	-172.199
3900MHz	0.979051	-178.471386	0.882176	41.94149	0.004415	-42.2875	0.882961	-172.247

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